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	Application No.	Applicant(s)	
Notice of Allowability	09/966,605	JIANG ET AL.	
	Examiner	Art Unit	
	Lan Vinh	1765	
The MAILING DATE of this communication ap All claims being allowable, PROSECUTION ON THE MERITS herewith (or previously mailed), a Notice of Allowance (PTOL-8 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT of the Office or upon petition by the applicant. See 37 CFR 1.3	S (OR REMAINS) CLOSED in (5) or other appropriate comm RIGHTS. This application is	n this application. If not include unication will be mailed in due	ded e course. <b>THIS</b>
1. This communication is responsive to <u>Amendment and re</u>	esponse filed on 4/19/2004.		
2. The allowed claim(s) is/are <u>1-15</u> .			
3. $\boxtimes$ The drawings filed on <u>28 September 2001</u> are accepted	by the Examiner.	•	
<ul> <li>4. Acknowledgment is made of a claim for foreign priority <ul> <li>a) All</li> <li>b) Some*</li> <li>c) None</li> <li>of the:</li> </ul> </li> <li>1. Certified copies of the priority documents hat 2. Certified copies of the priority documents hat 3. Copies of the certified copies of the priority of International Bureau (PCT Rule 17.2(a)).</li> <li>* Certified copies not received:</li> </ul> <li>Applicant has THREE MONTHS FROM THE "MAILING DATE noted below. Failure to timely comply will result in ABANDON THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.</li> <li>5. A SUBSTITUTE OATH OR DECLARATION must be sub INFORMAL PATENT APPLICATION (PTO-152) which generated by the Notice of Draftspet 1) hereto or 2) to Paper No./Mail Date</li> <li>(a) including changes required by the Notice of Draftspet 1) hereto or 2) to Paper No./Mail Date</li> <li>(b) including changes required by the attached Examined Paper No./Mail Date</li> <li>Identifying indicia such as the application number (see 37 CFF each sheet. Replacement sheet(s) should be labeled as such in 7. DEPOSIT OF and/or INFORMATION about the departached Examiner's comment regarding REQUIREMEN</li>	ave been received.  Ave been received in Application documents have been received.  E" of this communication to file NMENT of this application.  Demitted. Note the attached EX ives reason(s) why the oath or a sust be submitted.  Deriver's Amendment / Comment or a 1.84(c)) should be written on the the header according to 37 CH posit of BIOLOGICAL MAT	on No  Indicate the control of the drawings in the front (not the FR 1.121(d).  Indicate the control of the drawings in the front (not the FR 1.121(d).  Indicate the control of t	equirements  NOTICE OF
Attachment(s)  1. ☐ Notice of References Cited (PTO-892)  2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)  3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SE Paper No./Mail Date  4. ☐ Examiner's Comment Regarding Requirement for Deposition of Biological Material	6. Interview S Paper No. 3/08), 7. Examiner's	nformal Patent Application (PT nummary (PTO-413), /Mail Date Amendment/Comment Statement of Reasons for All  Lan Vinh AU 1765	

Application/Control Number: 09/966,605

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## Allowable Subject Matter

## 1. Claims 1-15 allowed.

The following is an examiner's statement of reasons for allowance:

Regarding claims 1, 11, the cited prior art of record fail to disclose a method for fabricating an integrated circuit comprises the step of treating said low k dielectric layer with a plasma having a bias power on the order of 400 W, wherein said treating step occurs in-situ with respect to said etching step/removing said via resist pattern using a plasma treatment to reduce poisoning by a nitrogen source, wherein said plasma treatment occurs in-situ with respect to said etching step and occurs under a bias power of approximately 400 W, in combination with the rest of the limitations of claims 1 and 11. One skilled in the art following the teaching of Hung et al (US 6,380,096) in view of Hsieh et al (US 6,455,431) would not have been motivated to operate the process of Hung at a bias power of 400 W. Hung teaches to perform the PET (post etch treatment ) at a bias power of no more than twenty percent of 1400 W (280W) (col 10, lines 55-58). Hung teaches that the low bias power desirable to eliminate copper sputtering (col 11, lines 59-64). As a result, one wishing to follow the teaching of Hung would utilize a bias power of no more than 280 W in order to avoid undesirable sputtering.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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## Conclusion

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 571 272 1471. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571 272 1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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May 21, 2004